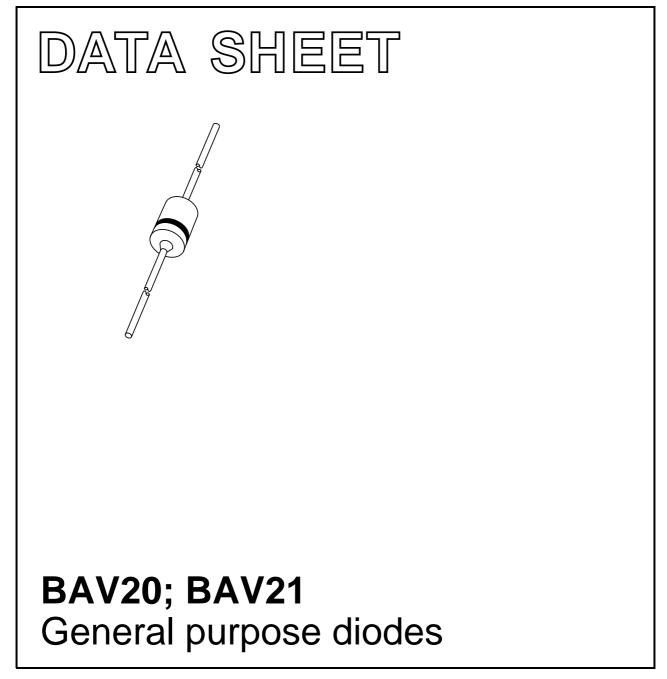
## DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1996 Sep 17 1999 May 25



## **BAV20; BAV21**

### FEATURES

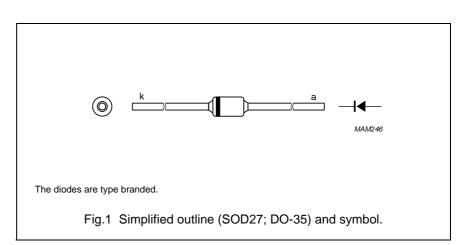
- Hermetically sealed leaded glass SOD27 (DO-35) package
- Switching speed: max. 50 ns
- General application
- Continuous reverse voltage: max. 150 V, 200 V
- Repetitive peak reverse voltage: max. 200 V, 250 V
- Repetitive peak forward current: max. 625 mA.

#### **APPLICATIONS**

 General purposes in industrial equipment e.g. oscilloscopes, digital voltmeters and video output stages in colour television.

#### DESCRIPTION

The BAV20 and BAV21 are switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD27 (DO-35) packages.



# BAV20; BAV21

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL           | PARAMETER                           | CONDITIONS   | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|--|------|------|------|
| V <sub>RRM</sub> | repetitive peak reverse voltage     |  |      |      |      |
|                  | BAV20                               |  | _    | 200  | V    |
|                  | BAV21                               |  | _    | 250  | V    |
| V <sub>R</sub>   | continuous peak reverse voltage     |  |      |      |      |
|                  | BAV20                               |  | _    | 150  | V    |
|                  | BAV21                               |  | _    | 200  | V    |
| IF               | continuous forward current          | see Fig.2; note 1  | _    | 250  | mA   |
| I <sub>FRM</sub> | repetitive peak forward current     |  | -    | 625  | mA   |
| I <sub>FSM</sub> | non-repetitive peak forward current | square wave; T <sub>j</sub> = 25 °C prior to<br>surge; see Fig.4 |      |      |      |
|                  |                                     | t = 1 μs   | _    | 9    | А    |
|                  |                                     | t = 100 μs   | _    | 3    | А    |
|                  |                                     | t = 1 s  | _    | 1    | А    |
| P <sub>tot</sub> | total power dissipation             | T <sub>amb</sub> = 25 °C; note 1                                 | _    | 400  | mW   |
| T <sub>stg</sub> | storage temperature                 |  | -65  | +175 | °C   |
| Tj               | junction temperature                |  | -    | 175  | °C   |

#### Note

1. Device mounted on an FR4 printed circuit-board; lead length 10 mm.

## BAV20; BAV21

### ELECTRICAL CHARACTERISTICS

 $T_j = 25 \ ^{\circ}C$  unless otherwise specified.

| SYMBOL          | PARAMETER             | CONDITIONS  | MIN. | MAX. | UNIT |
|-----------------|-----------------------|---|------|------|------|
| V <sub>F</sub>  | forward voltage       | see Fig.3   |      |      |      |
|                 |                       | I <sub>F</sub> = 100 mA   | _    | 1.0  | V    |
|                 |                       | I <sub>F</sub> = 200 mA   | _    | 1.25 | V    |
| I <sub>R</sub>  | reverse current       | see Fig.5   |      |      |      |
|                 |                       | $V_{R} = V_{Rmax}$  | -    | 100  | nA   |
|                 |                       | V <sub>R</sub> = V <sub>Rmax</sub> ; T <sub>j</sub> = 150 °C  | -    | 100  | μA   |
| C <sub>d</sub>  | diode capacitance     | $f = 1 MHz; V_R = 0; see Fig.6$   | -    | 5    | pF   |
| t <sub>rr</sub> | reverse recovery time | when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100 \Omega$ ; measured at $I_R = 3$ mA; see Fig.8 | _    | 50   | ns   |

### THERMAL CHARACTERISTICS

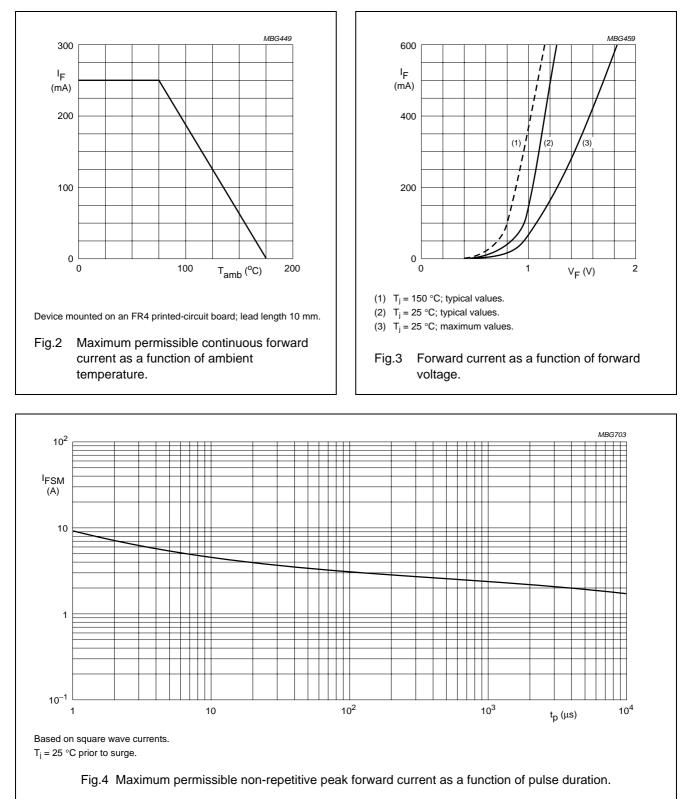
| SYMBOL               | PARAMETER                                     | CONDITIONS                | VALUE | UNIT |
|----------------------|---|---------------------------|-------|------|
| R <sub>th j-tp</sub> | thermal resistance from junction to tie-point | lead length 10 mm         | 240   | K/W  |
| R <sub>th j-a</sub>  | thermal resistance from junction to ambient   | lead length 10 mm; note 1 | 375   | K/W  |

Note

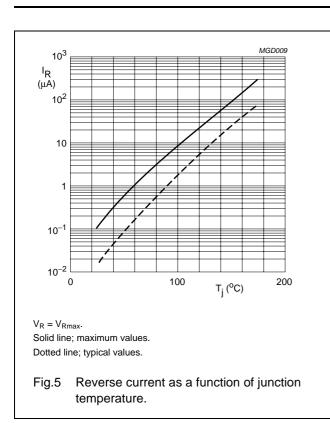
1. Device mounted on a printed circuit-board without metallization pad.

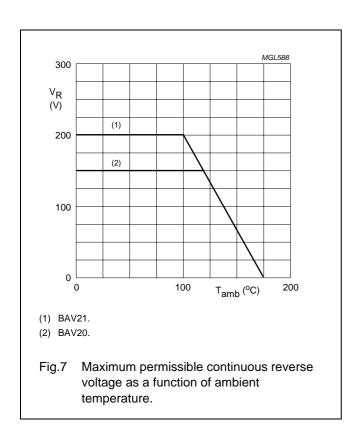
### BAV20; BAV21

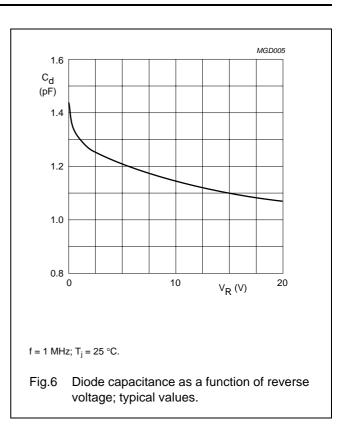
#### **GRAPHICAL DATA**



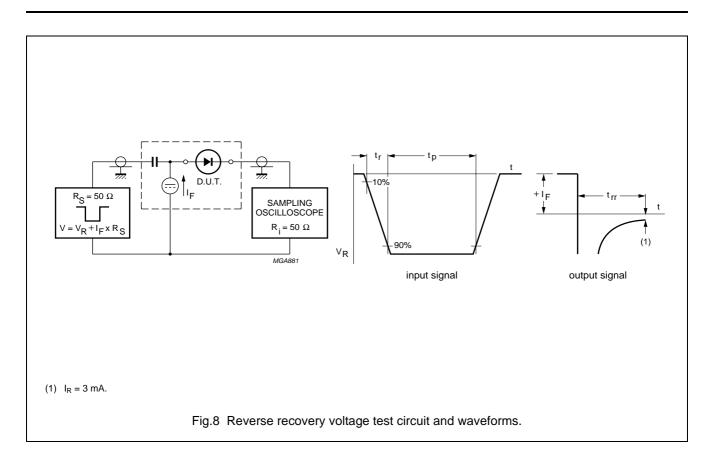
## BAV20; BAV21





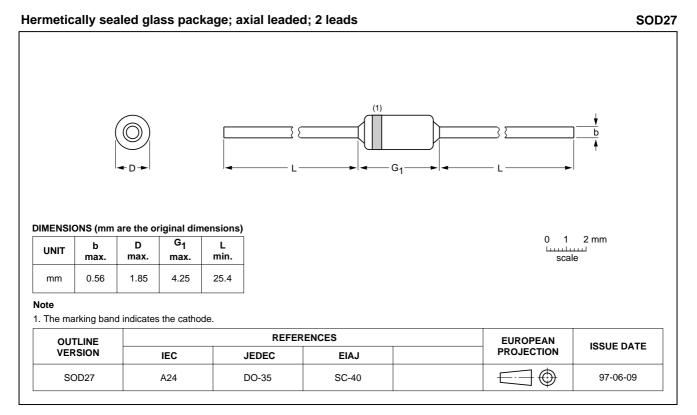


# BAV20; BAV21



## BAV20; BAV21

#### PACKAGE OUTLINE



### **BAV20; BAV21**

| DOCUMENT<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION  |
|-----------------------------------|----------------------------------|---|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet            | Qualification                    | This document contains data from the preliminary specification.                       |
| Product data sheet                | Production                       | This document contains the product specification.                                     |

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#### **Contact information**

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